



Production and Testing of the LHCb Outer Tracker Front End Readout Electronics

Eduard Simioni, NIKHEF

On Behalf of the LHCb OT group

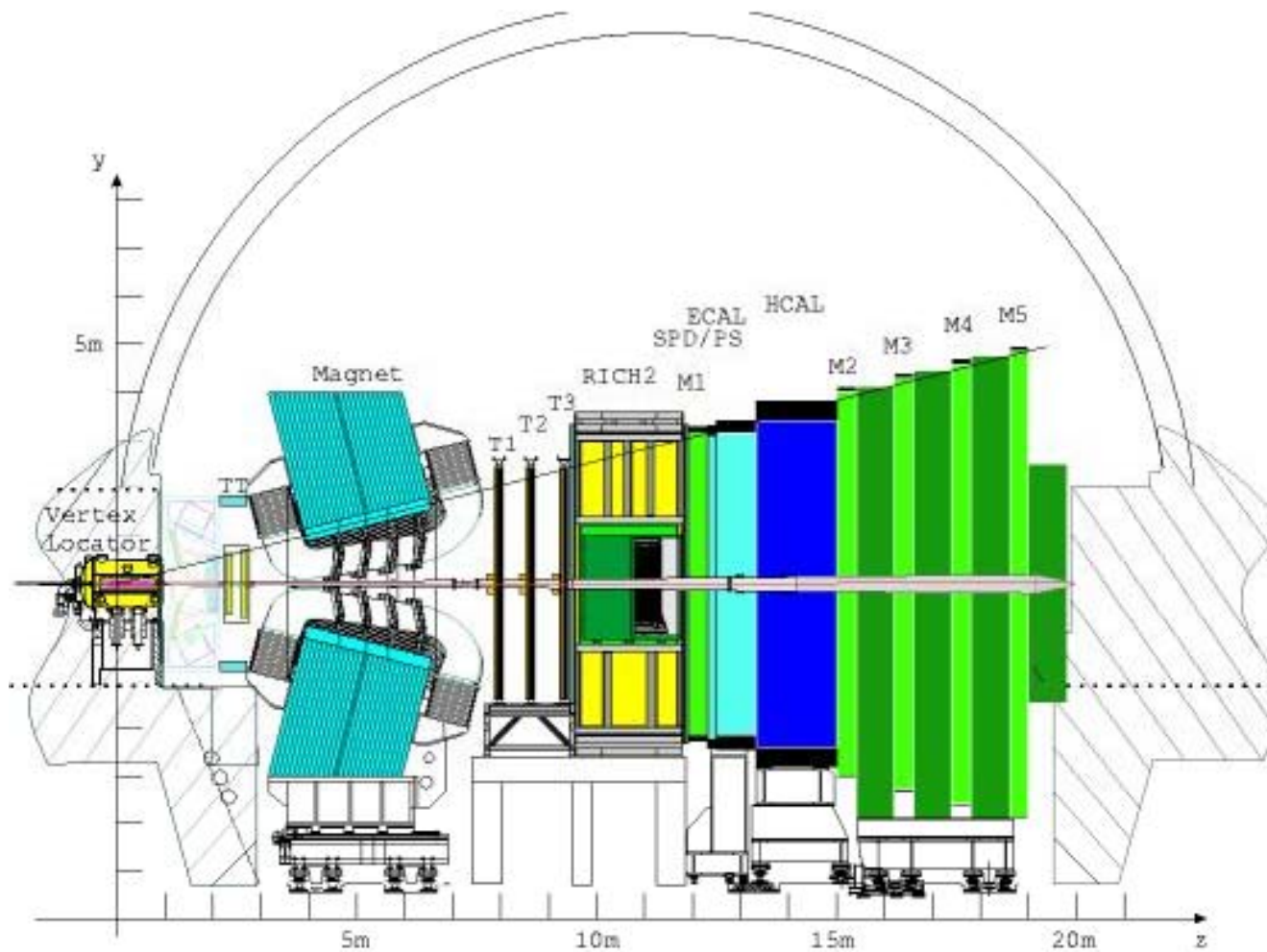
NIKHEF, National Institute of high energy physics: Amsterdam, The Netherlands
Physikalisches Institut: Heidelberg, Germany

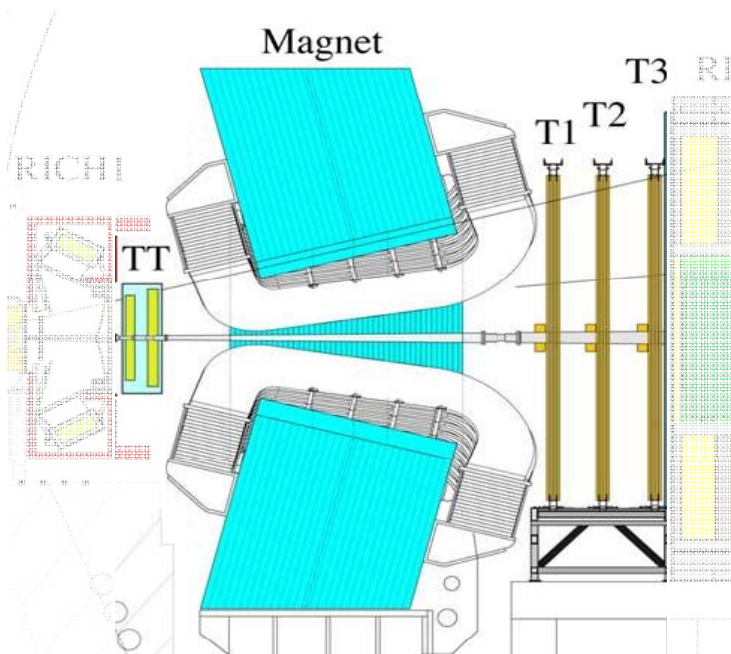
Henryk Niewodniczanski Institute of Nuclear Physics: Cracow, Poland

Andrzej Soltan Institute for Nuclear Studies: Warsaw, Poland

Tsinghua University: Beijing, China

- **LHCb and the Outer Tracker sub-detector**
- **FE Electronics Overview**
- **Quality Assurance**
- **Commissioning of the FE-Box**
- **Summary**





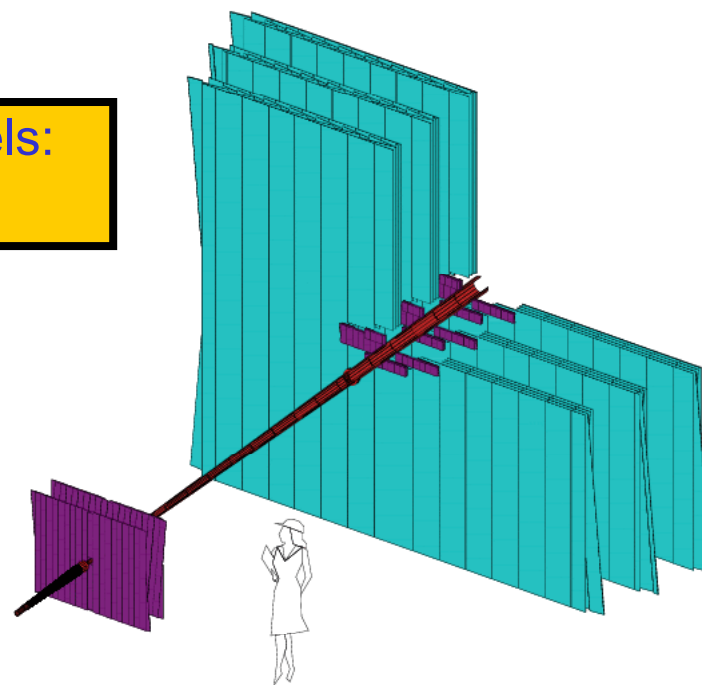
3 OT Stations T1,T2,T3, modular design.

Each OT Station consists of 4 planes XUVX.

B-Field vertical, (measure x-coordinate)

$qU,V = \pm 5^\circ$

**Total channels:
>56.000**

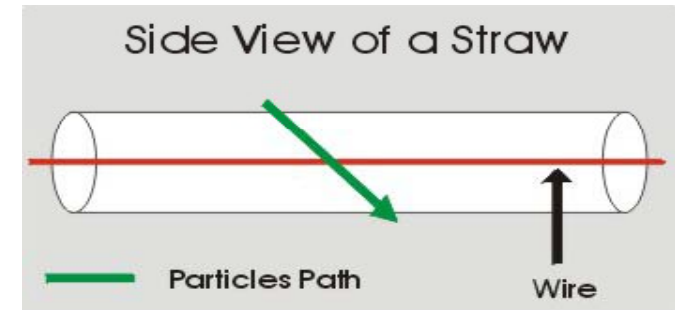


Along the Beam pipe (1%): High-flux region

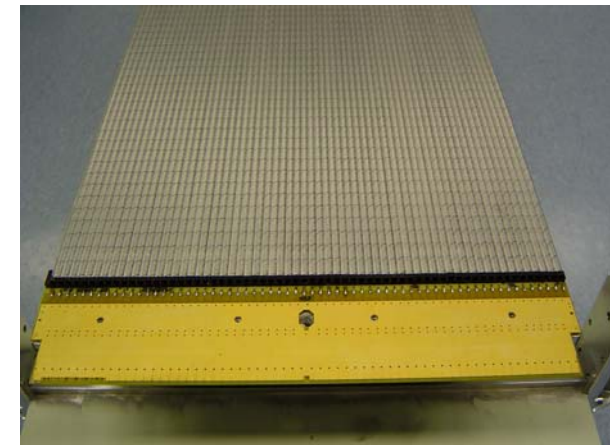
(Vertex, trigger and inner tracker)

Remaining Area (99%): straw drift-tubes

(Outer Tracker)



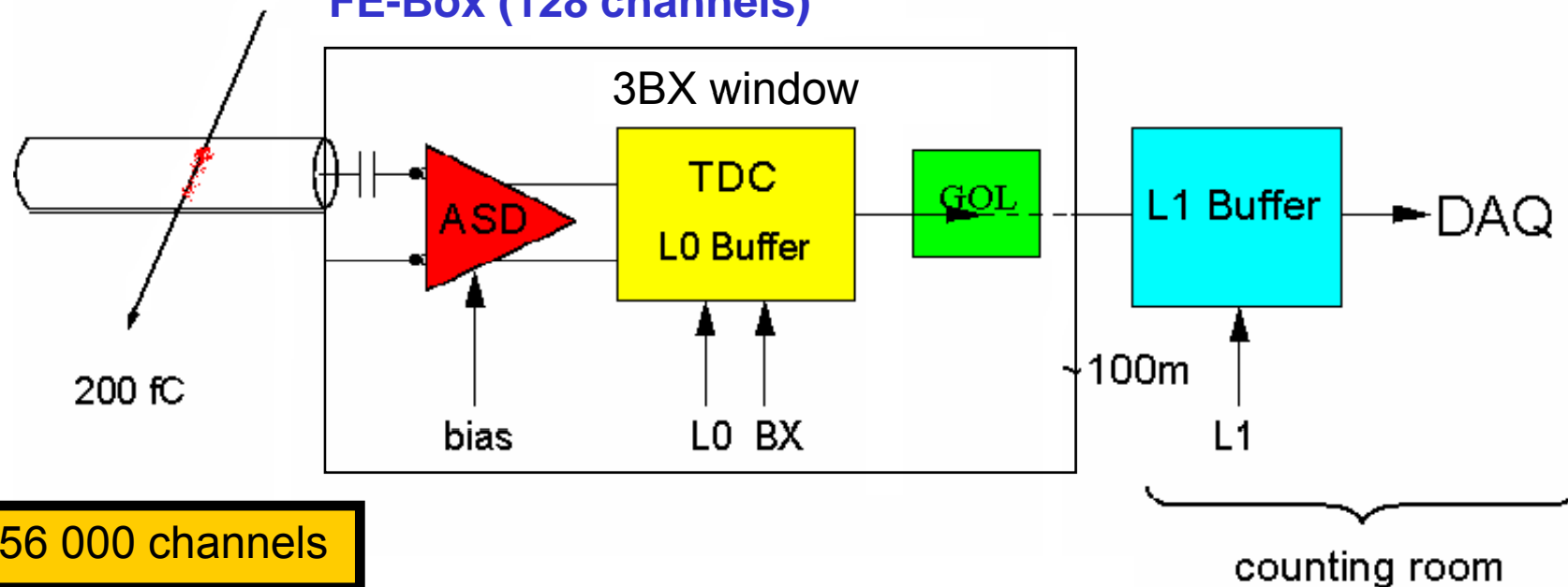
- A straw tube, (**5mm** \varnothing), is wound from two layers of foil material, (carbon-doped kapton and aluminum).
- Gold plated tungsten wires (**25 mm** \varnothing).
- Gas mixture **Ar/CO₂** in ratio 70/30
- Two mono-layers of **64** straw tubes each
- **Two** sandwich panels to support the straw tubes
- **Two** side walls to seal the gas box



Extremely Light-Weight Structure (crucial for tracking!)

- Total weight in sensitive area: **6.8 kg**
- Total radiation length X/X_0 : **0.37%**

FE-Box (128 channels)



~ 56 000 channels

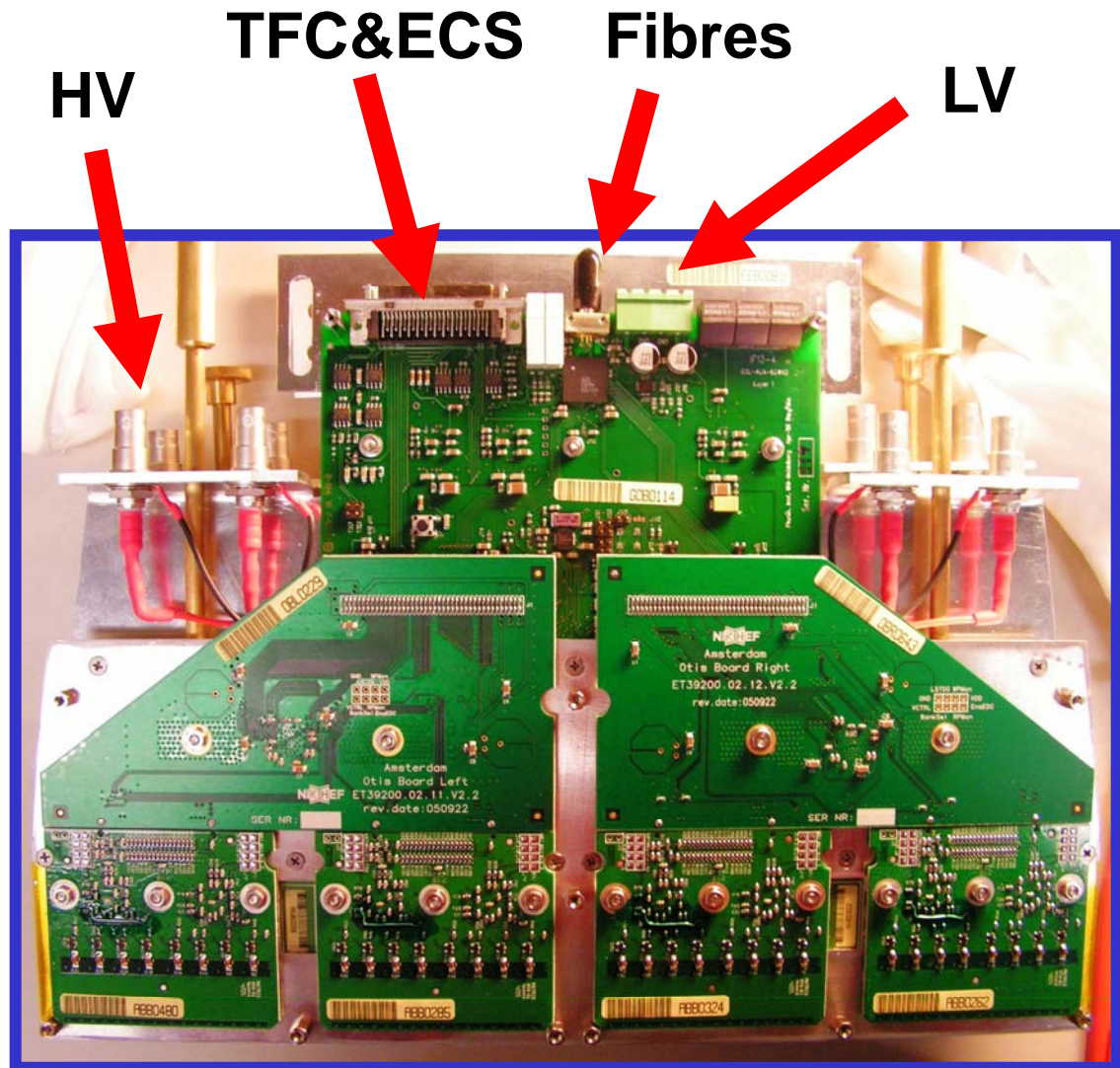
- **Amplify** analog signals from anode wires (ASDBLR board)
- **Digital** conversion (ASDBLR board)
- **Drift Time** measurement (OTIS board)
- **Data optical link and services** (GOL board)

MASS PRODUCTION:

- 500** GOL/AUX Boards
- 2.000** OTIS TDC Boards
- 4.000** ASDBLR Boards
- 2.000** HV Boards

Front end box (full size):

- 128 channels
- 16 ASDBLR chips
- 4 OTIS TDC chips
- 1 optical link: 1.6 Gbit/s



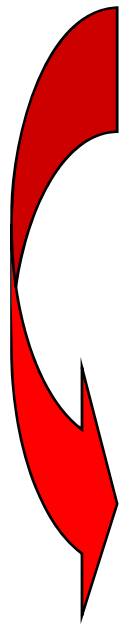
- **HV board :**
 - Visual Inspection of bare PCB (alignment holes)
 - Thickness measurement of the bare PCB
 - Leackage and capacitance long term burn-test in a hoven
- **ASDBLR board :**
 - ASDBLR ICs Selection (~40% used ⇒ **single Thr sub-detector!**)
 - Visual inspection of the input/output connectors
- **OTIS Board :**
 - OTIS ICs selection
 - Visual Inspection of bare PCB
 - Visual inspection of the input/output connectors
 - Bonding and test (before and after globtop)
- **GOL Board :**
 - Dedicated Setup for GOL board-testing
- **FE-Chassis**
 - Mechanical and electrical check

All test informations collected in a DataBase (important to track back problems)

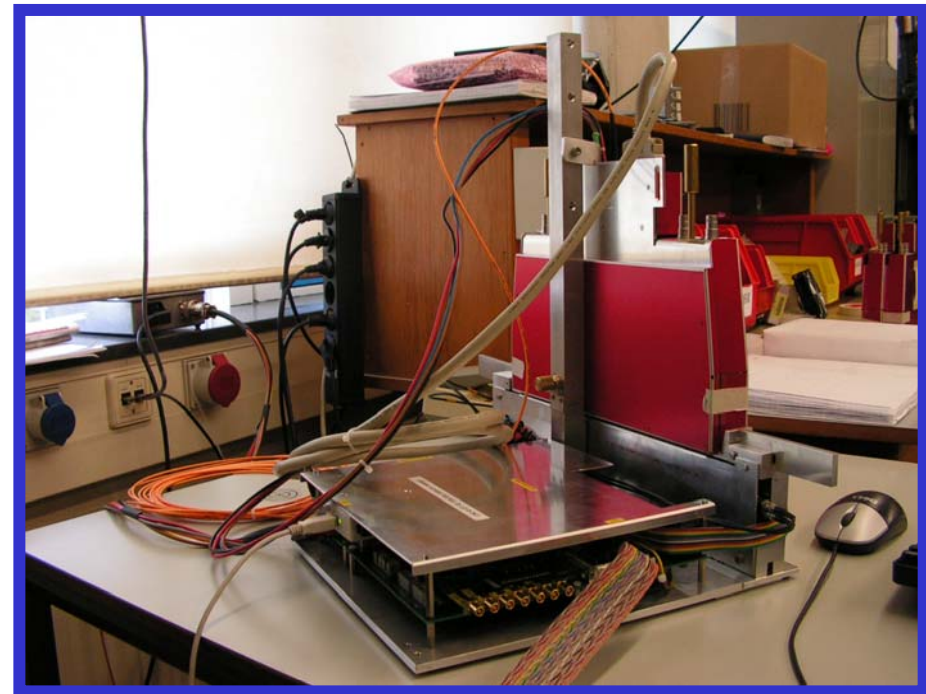
FE-Setup for commissioning of a completed FE-Boxes

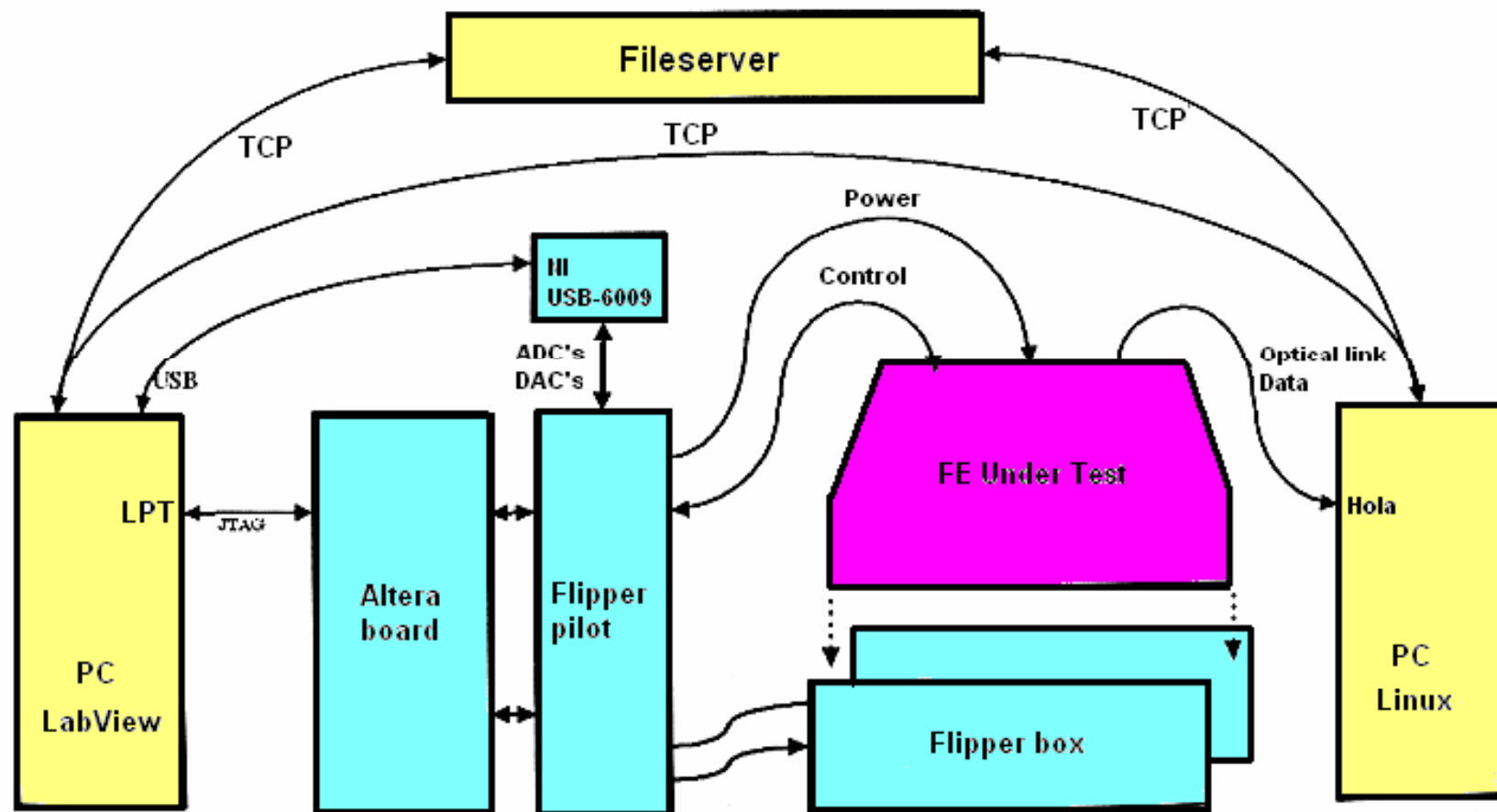
Test of global functionality of FE-Boxes, requirements:

- Analog input signal injection (mimicking the straw-like signal)
- Generation of ECS & TFC
- Data Acquisition (Fiber \Rightarrow Disk)
- High time accuracy (~ 0.15 ns)



Threshold Scan
ASDBLR TestPulses (high and low)
Input delay Scan
Signal amplitude Scan
L0 (latency scan)
Ect...





- **Threshold characteristics :**

 - Amplitude Scan with **input signal** $\Rightarrow V_{thr}^{50\%}$, noise, cross-talk etc...

 - Thr Scan with **input signal** $\Rightarrow V_{thr}^{50\%}$, noise, cross-talk etc...

 - Thr Scan with **Test-Pulse Low** $\Rightarrow V_{thr}^{50\%}$, noise, cross-talk etc...

 - Thr Scan with **Test Pulse High** $\Rightarrow Q_{thr}^{50\%}$, noise, cross-talk etc...

- **Noise :**

 - Thr Scan with no **input signal**

- **Timing :**

 - Drift-time spectra of all channels

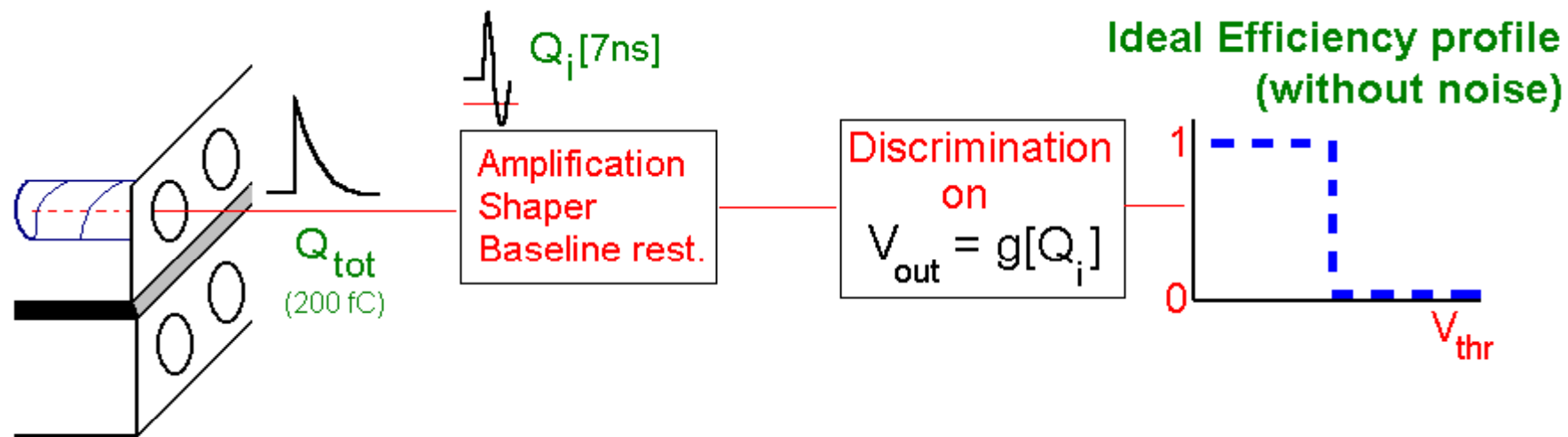
 - Delay scan over the full time range

- **L0 scan :**

 - L0 Delay Scan in steps of $\frac{1}{2}$ BX

- **Analysis**

 - Control histograms automatically generated for all tests



For a Gaussian Noise Distribution

$$Pr[V_{thr}, Q_i] = \int_{V_{thr}}^{+\infty} f[V] dV = N \int_{V_{thr}}^{+\infty} e^{-\frac{1}{2} \frac{(V - g[Q_i])^2}{(s_{noise})^2}} dV$$

$$Pr[V_{thr}, Q_i] = \frac{1}{2} - \frac{1}{2} \text{Erf} \left[\frac{V_{thr} - g[Q_i]}{\sqrt{2} s_{noise}} \right]$$

$$Pr[V_{thr}, Q_i] = \frac{1}{2} - \frac{1}{2} \text{Erf} \left[\frac{V_{thr} - g[Q_i]}{\sqrt{2} s_{noise}} \right]$$

if $V_{thr} = g[Q_i]$

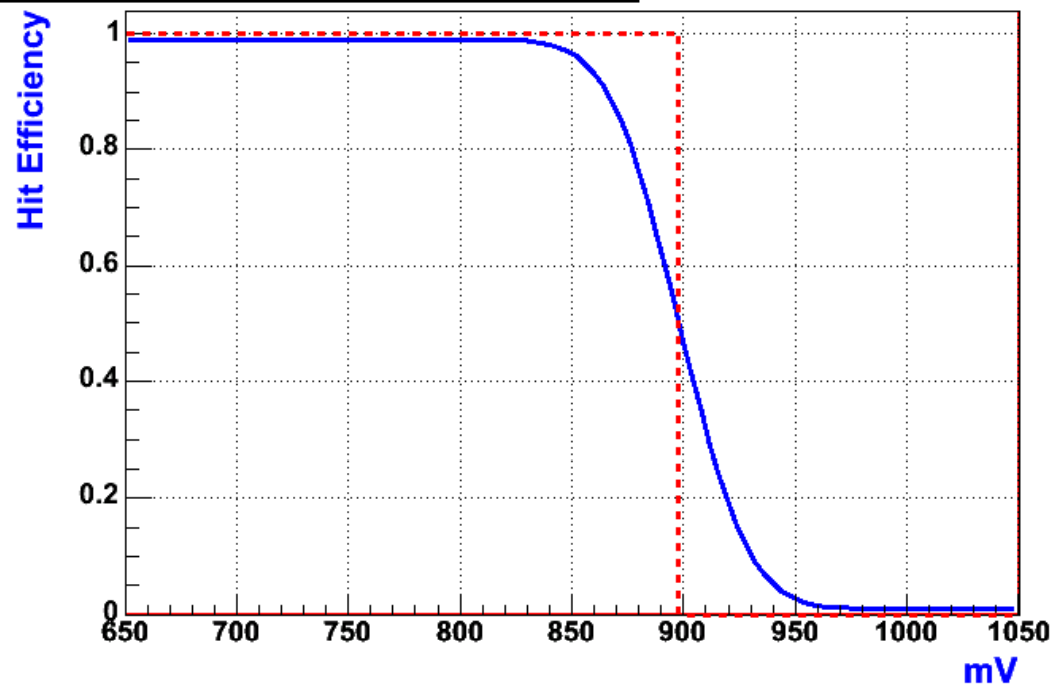
$$Pr[g[Q_i], Q_i] = 0.5$$



$V_{thr}^{[50\%]}$

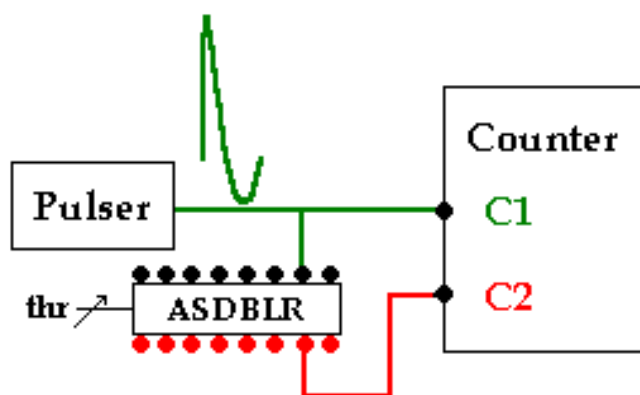
best estimator of $g(Q_i)$

0.50-0.49*TMath::Erf((x-898)/34.6)

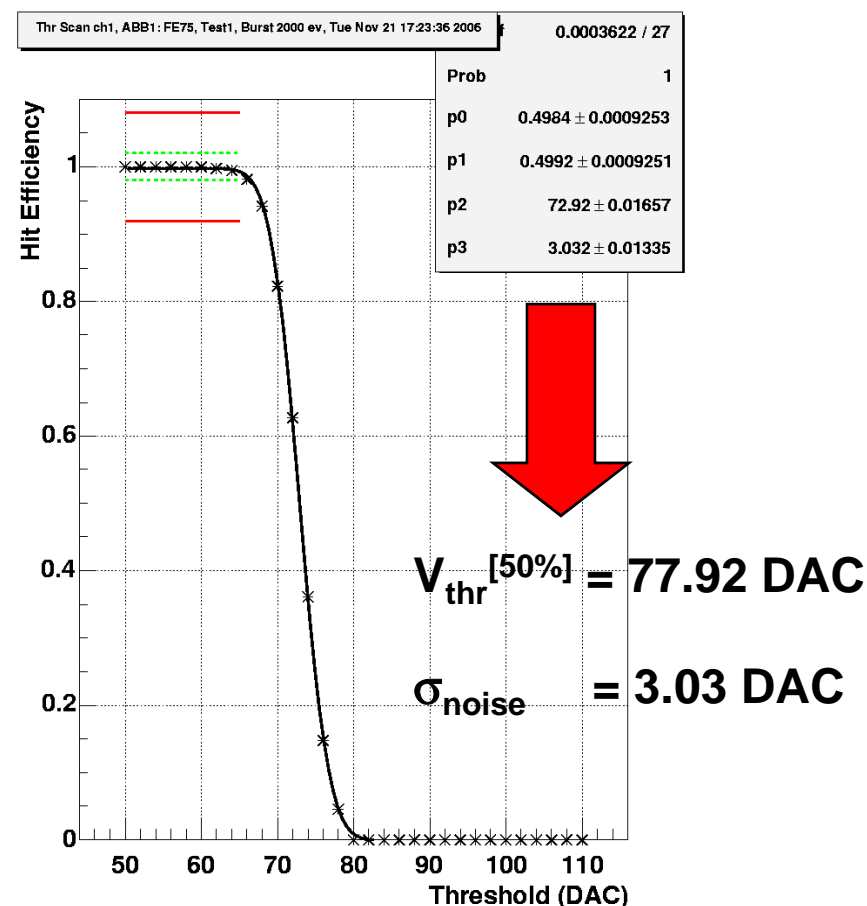


Measure the hit efficiency profile for each channel, fit erf model to data and determine $V_{thr}^{[50\%]}$ and σ_{noise}

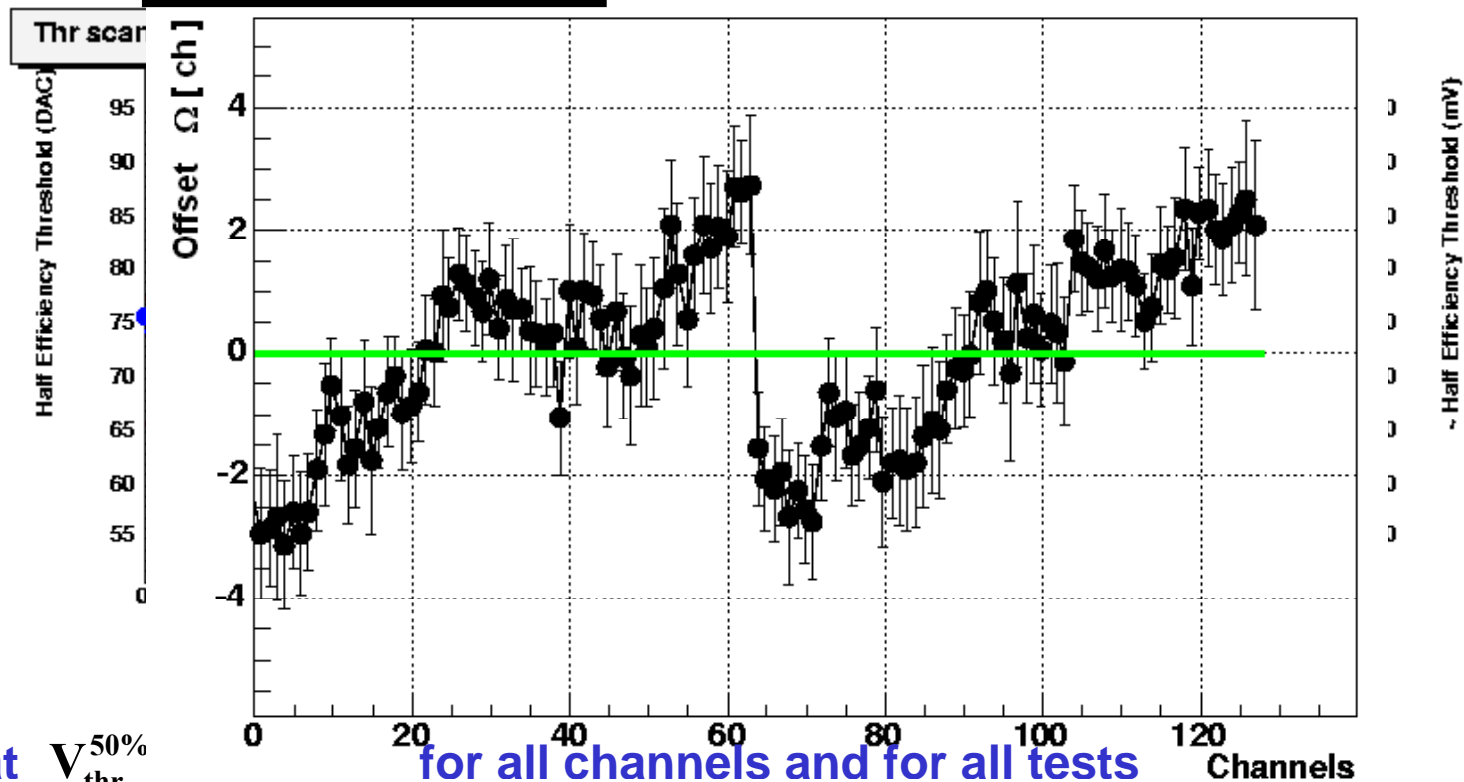
Hit Efficiency = C2 / C1



Channel to channel uniformity expected to be within ~50 mV



Preliminary

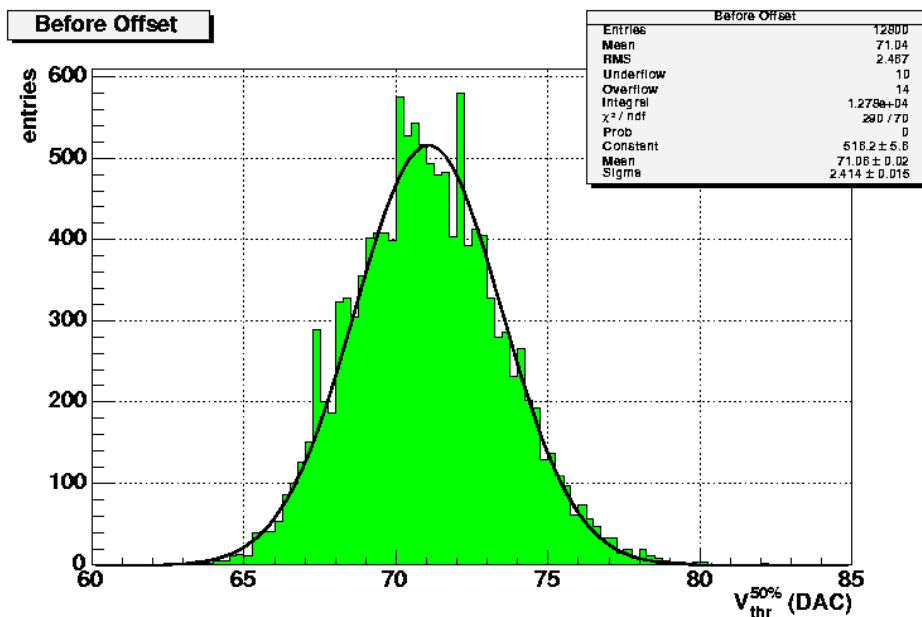


Look at $V_{thr}^{50\%}$

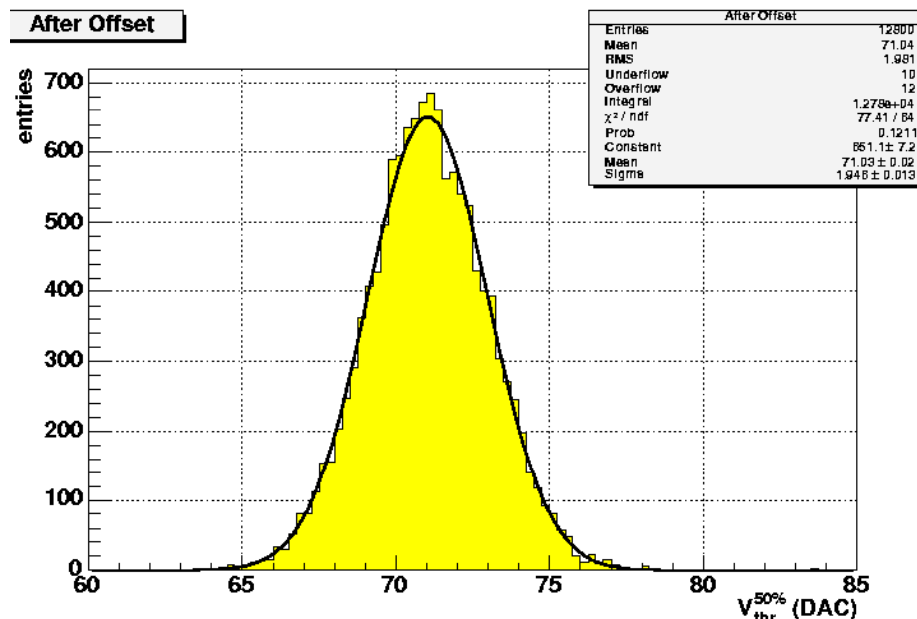
for all channels and for all tests

Define correction offsets:

$$\Omega[\text{ch}] = \frac{\sum_{\text{ch}} \sum_{\text{Tests}} V_{thr}^{50\%} [\text{ch}, \# \text{Test}]}{128 N_{\text{Tests}}} - \frac{\sum_{\text{Tests}} V_{thr}^{50\%} [\text{ch}, \# \text{Test}]}{N_{\text{Tests}}}$$



- $V_{\text{thr}}^{50\%}$ Distribution before Offset Corrections



- $V_{\text{thr}}^{50\%}$ Distribution after Offset Corrections

Powerful Check:

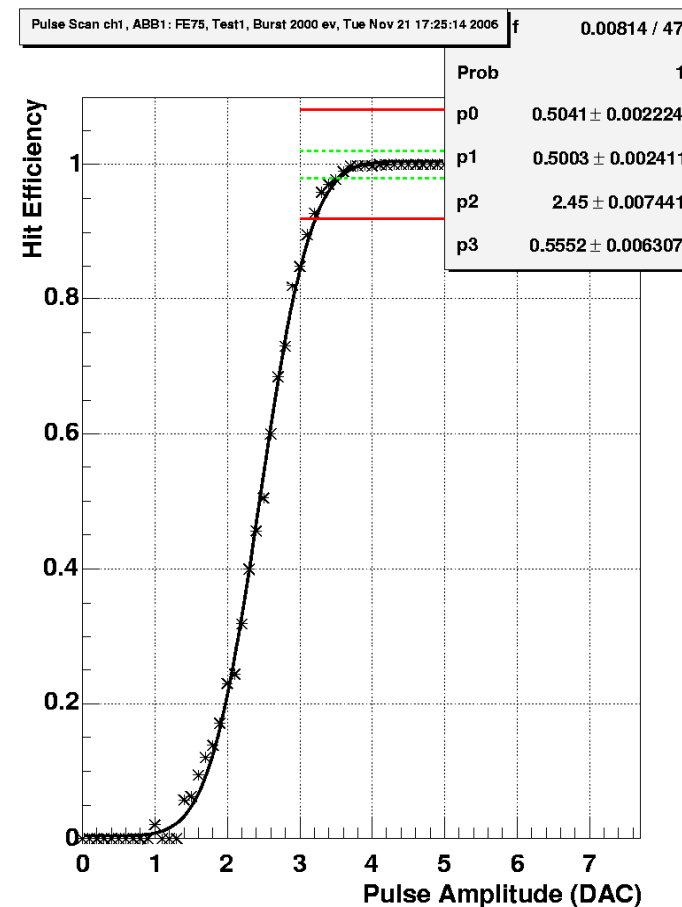
- Large deviating or broken channels found: due to missing component, shorts on the connectors, bad chip soldering ect...
- Amazing uniformity (**we gonna use one threshold for all the discriminators**)

- Fixed **threshold** of ~800 mV,
Burst length of 2000 events

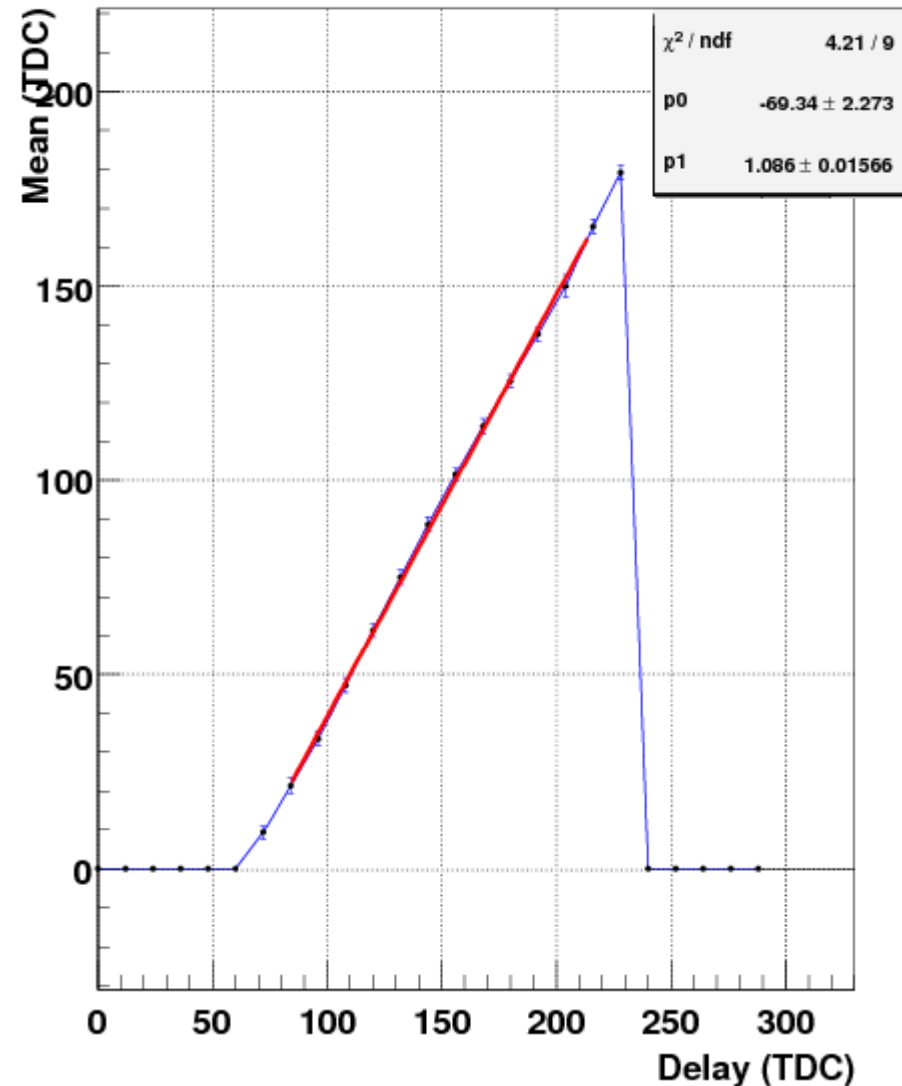
$$Pr[V_{thr}, Q_i] = \frac{1}{2} + \frac{1}{2} \text{Erf} \left[\frac{Q_i - Q_{thr}}{\sqrt{2} \text{ENC}} \right]$$

- **Fit error function** to data points for **each channel**
 - Half-Efficiency Amplitude
 - Width (σ)
 - Chi2 (χ^2)

- **Q_{thr}** Global Uniformity
- **ENC** Direct measurement of Equivalent Noise Charge (fC)



- Fixed **threshold** of ~ 800 mV,
Fixed **charge** of ~ 6 fC
Burst length of 2000 events
- **Fit linear function** to data points for **each channel**
- Reject if:
 - Offset deviant from other channels.
 - Large χ^2 /Bad data



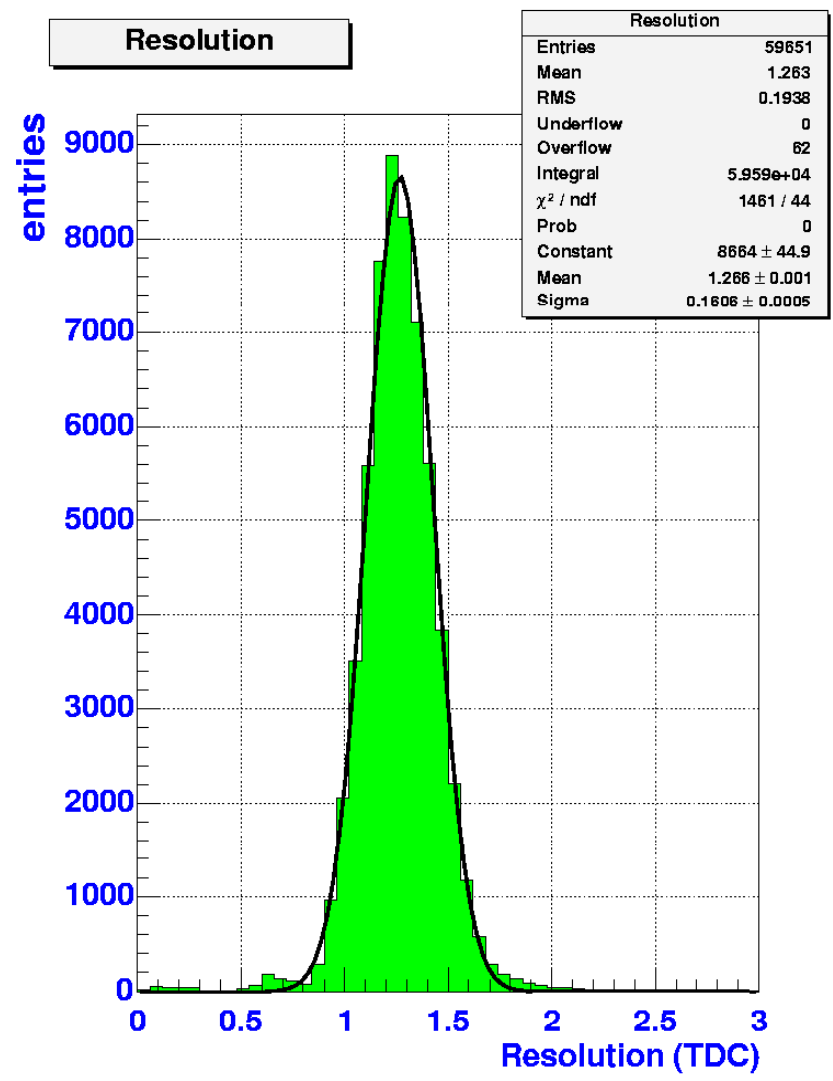
Average result over 50 FE Boxes:

1.27 ± 0.16 TDC channels

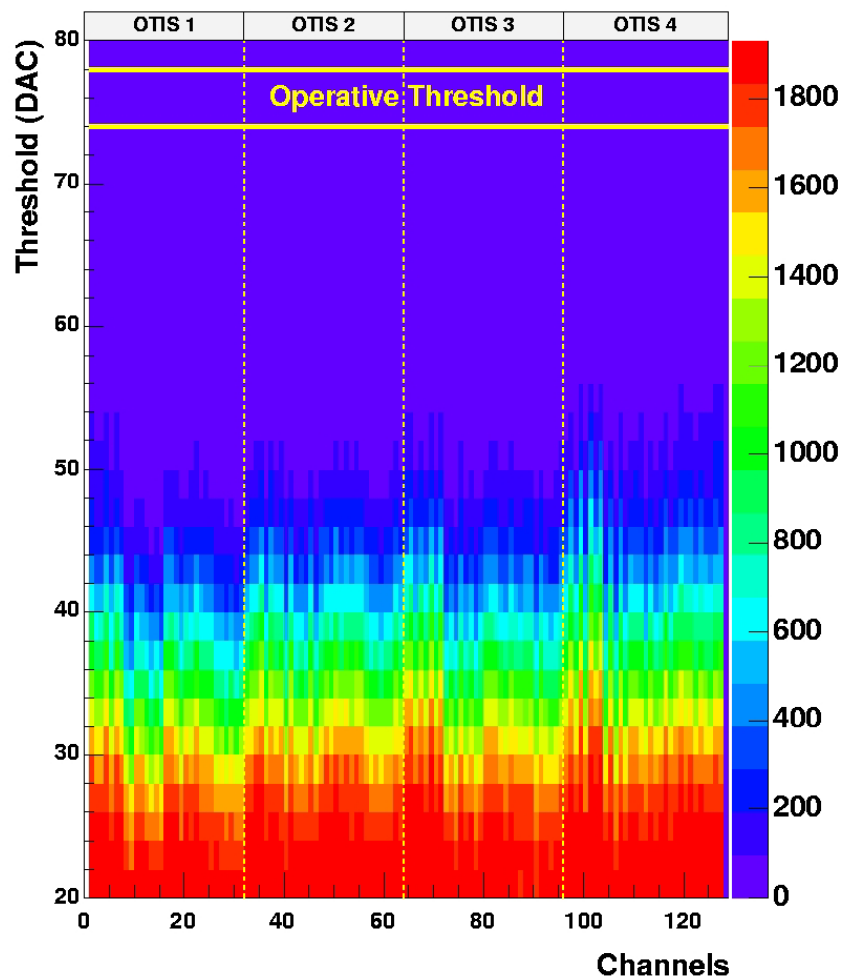
i.e.:

0.496 ± 0.062 ns

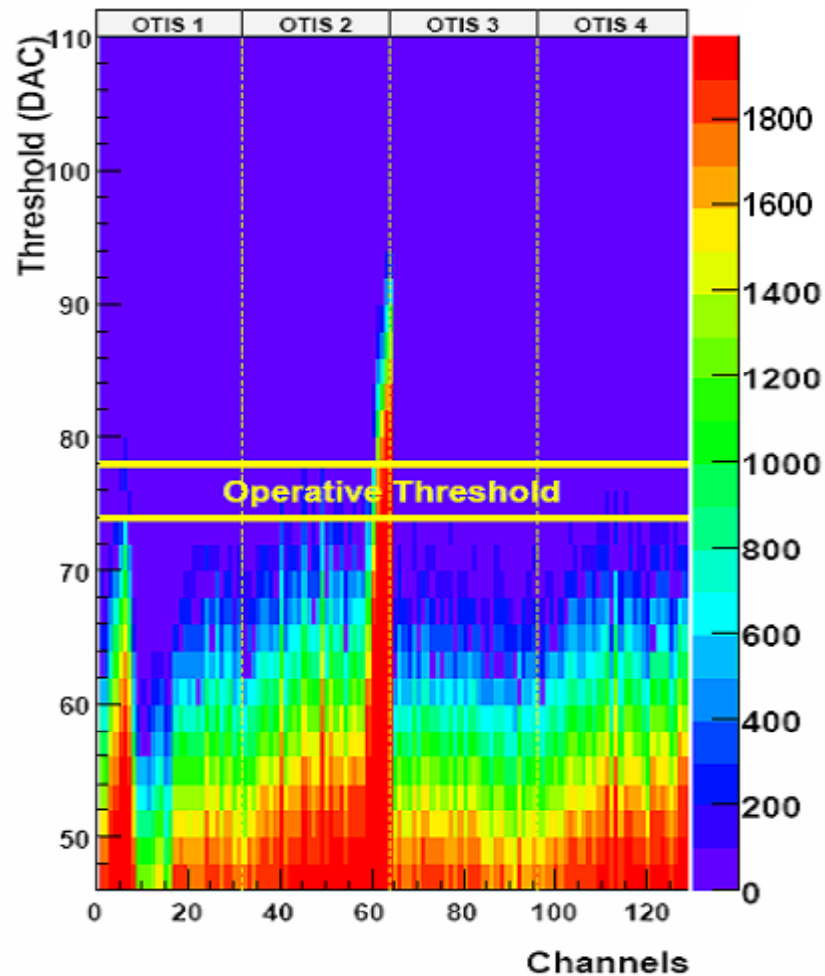
(includes contribution of input-pulse timing resolution, etc.)

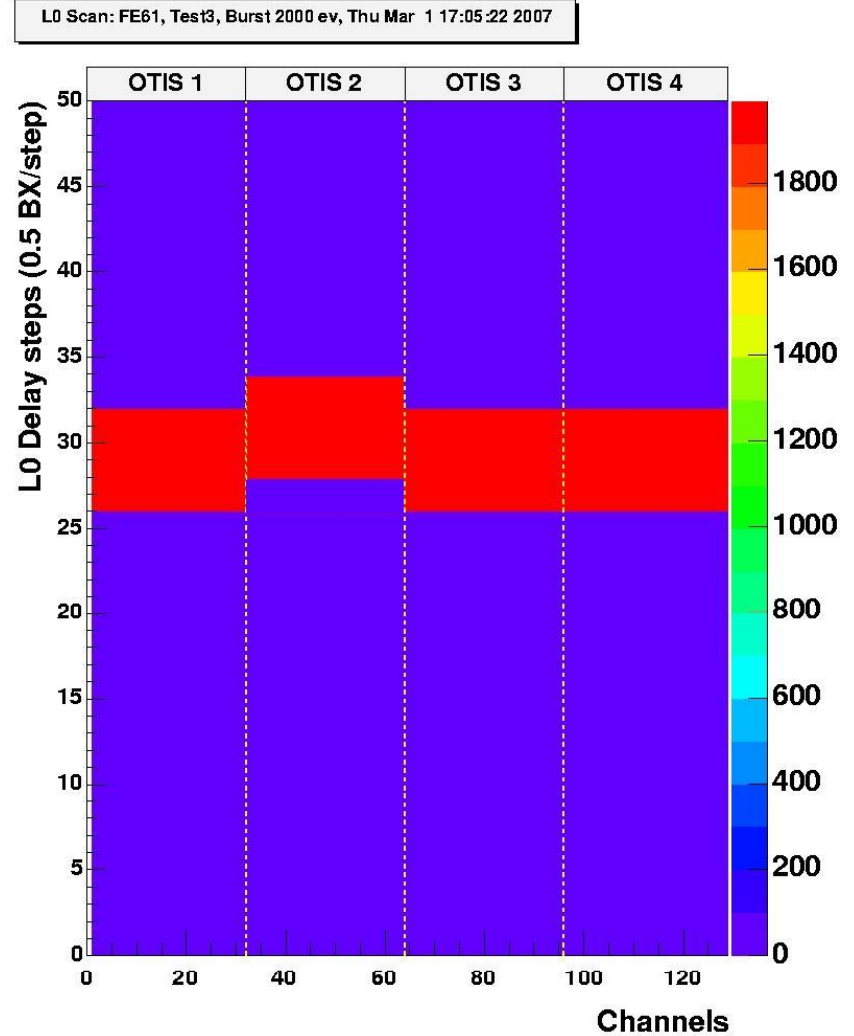
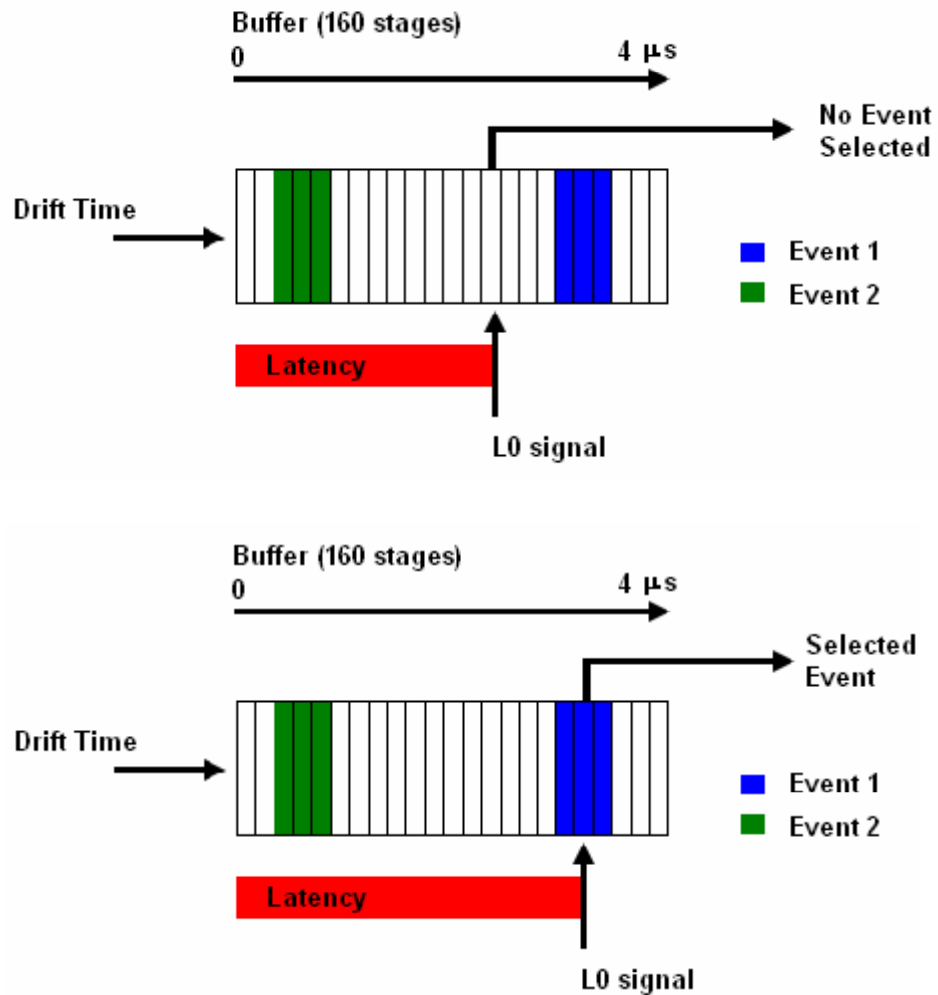


Noise Map Thr Scan: FE61, Test3, Burst 2000 ev, Thu Mar 1 17:04:38 2007



CT Map Thr Scan: FE112, Test1, Burst 2000 ev, Wed May 30 15:38:22 2007



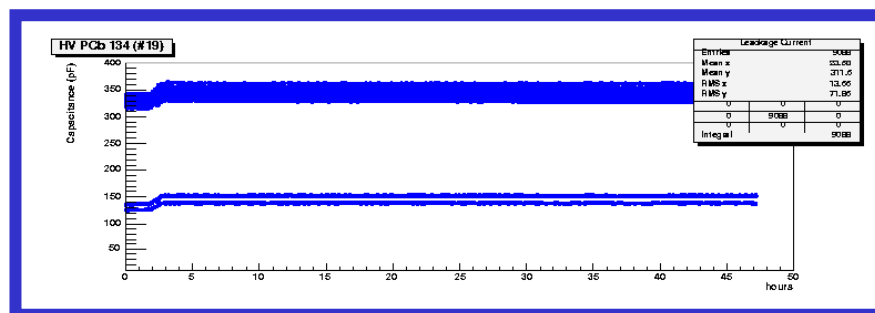
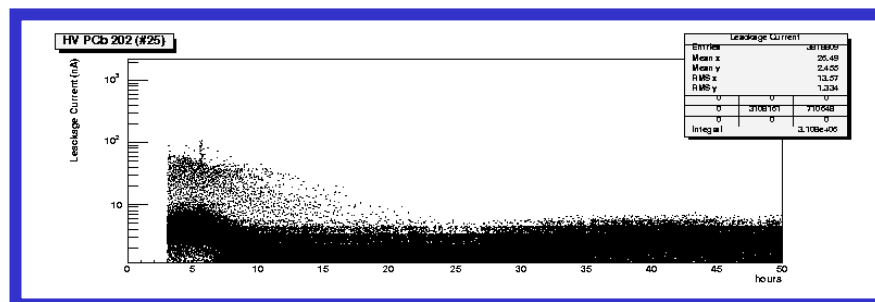
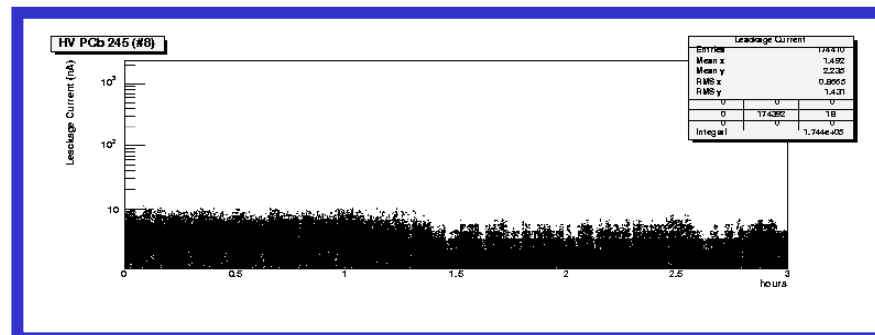


- Boards **production&test** completed in June 2007
- FE Production at NIKHEF of the LHCb Outer Tracker electronics is **currently at Regime:**
 - **~210 / (~50%)** FE-Boxes assembled and tested
 - **36 FE-Boxes** installed and tested in situ
- Excellent and compact test-of-performance of the Read-Out achieved using the **FE-Tester Setup** (important in the R&D phase)
- **Electronics partially installed on the Outer-Tracker:** used for a first commissioning of the electronics chain (straw \Rightarrow Counting room)
- A FE-Setup will be kept in the LHCb pit for FE-Testing and hardware debugging



Additional Slides





Test for:

Capacitance

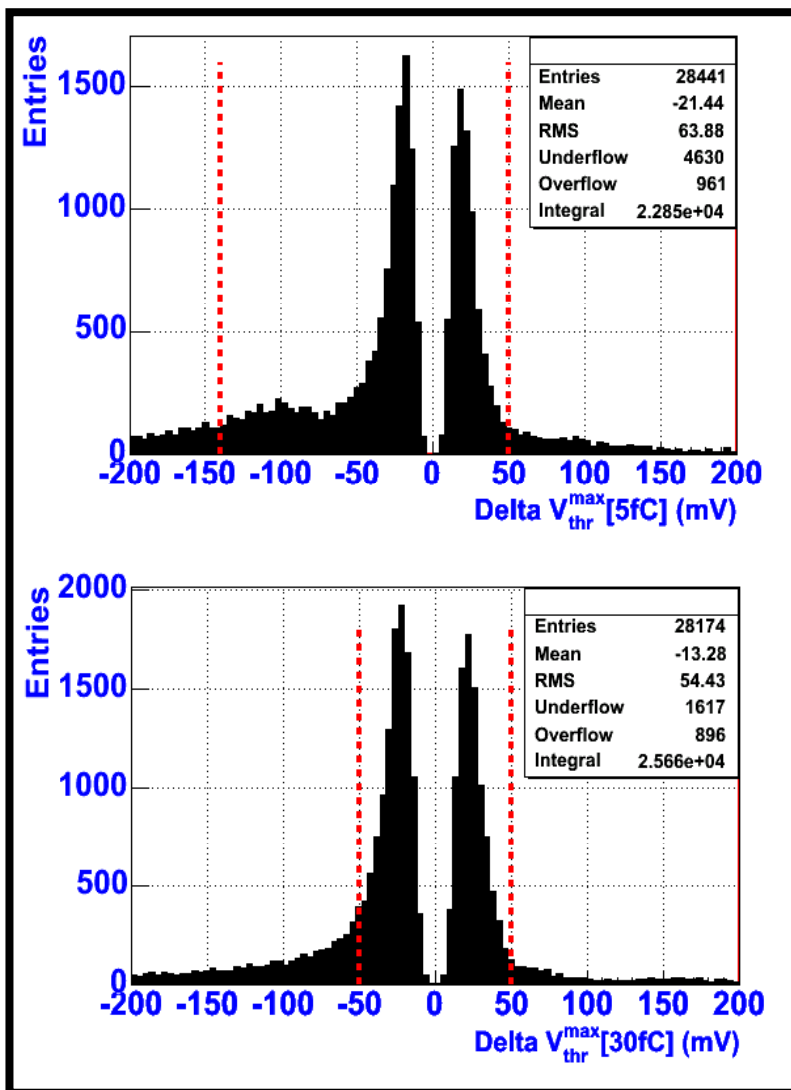
Leakage Current

Settings

- 48 hours
- 2000 Volt
- 70° C

Cut	Test	Losses	Survivors (%)
T1	<i>Input Resistance</i>	1738	94.10
T2	<i>Supply Current (P)</i>	2015	87.26
T3	<i>Supply Current (N)</i>	102	86.91
T4	<i>BLR Monitor</i>	46	86.75
T5	<i>Diode Voltage</i>	119	86.35
T6	<i>Input Current</i>	272	85.43
T7	<i>Output Current</i>	131	84.98
T8	<i>Output Switch</i>	2678	75.89
T9	<i>Broken Channels</i>	4023	62.23

Cut	Test	Losses	Survivors (%)
T1-T9	<i>Pre-Selection</i>	11124	62.23
T10	<i>Half Efficiency</i>	5690	42.90



Deviation Parameter

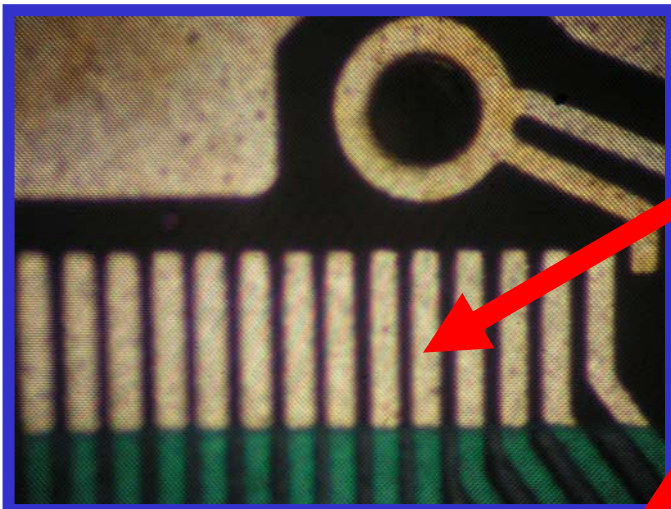
$$\Delta V_{thr}^{[50\%]}[j] = 1/8 \sum_j V_{thr}^{[50\%]} [j] - V_{thr}^{[50\%]} [j]$$

Max Deviation Parameter

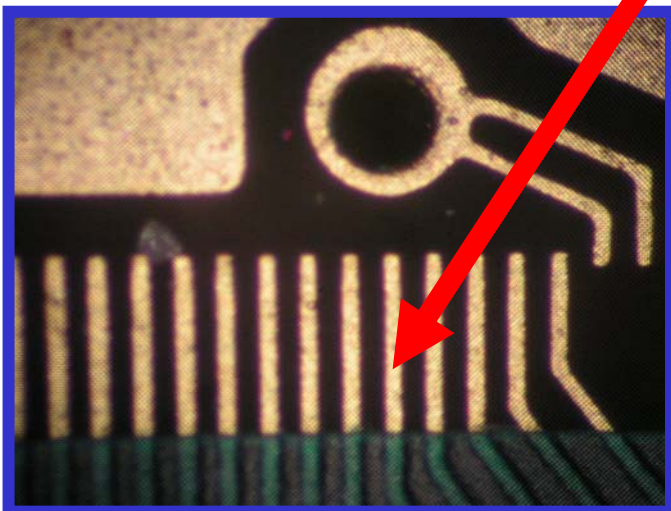
$$\Delta V_{thr}^{max} = \text{Max}_{j \in \{1;8\}} \{ \Delta V_{thr}^{[50\%]}[j] \}$$

Performed:

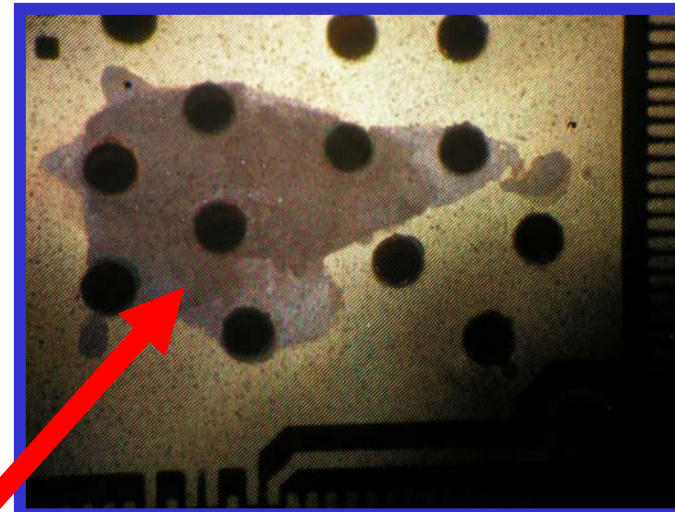
- * For each chip
- * Foreach Charge injected



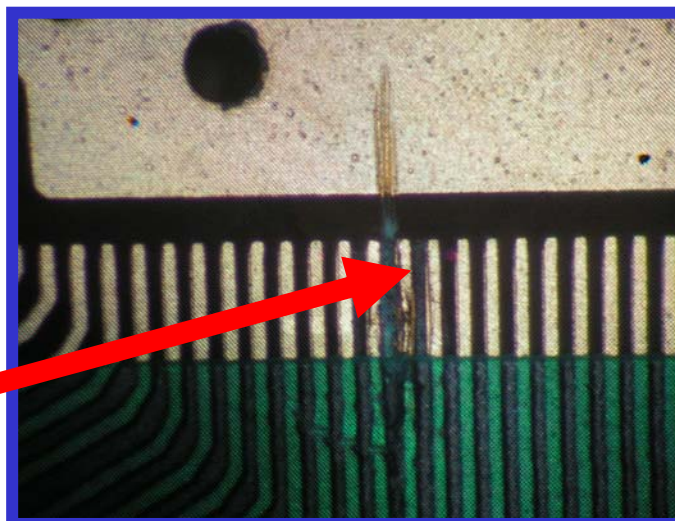
Good bonding pads



Bad (**thin**) bonding pads



Spot on grounding plane



Short

Test procedure for each chip:

power consumption ok? ($I < 300\text{mA}@2.5\text{V}$)

Slow control test: Check position ID and registers

FPGA test:

Chip alive?

Header ok?

All channels alive?

Measurement of DNL for channel 0, 15, 16, 31

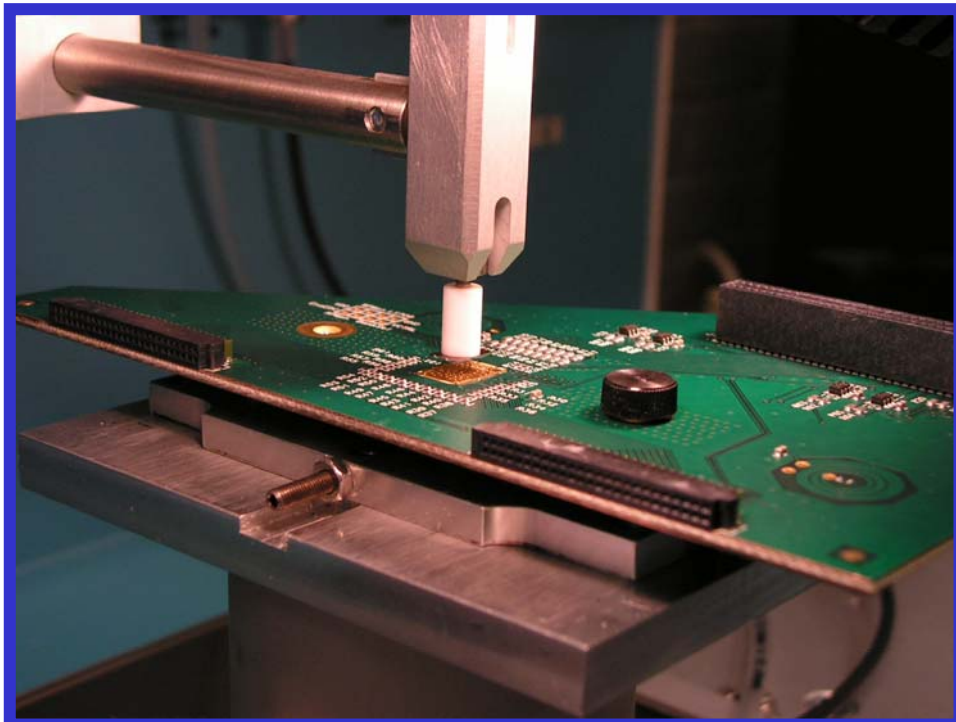
(DNL < 2.0 bins for OTIS 1.2 and

DNL < 1.9 bins for OTIS 1.3,

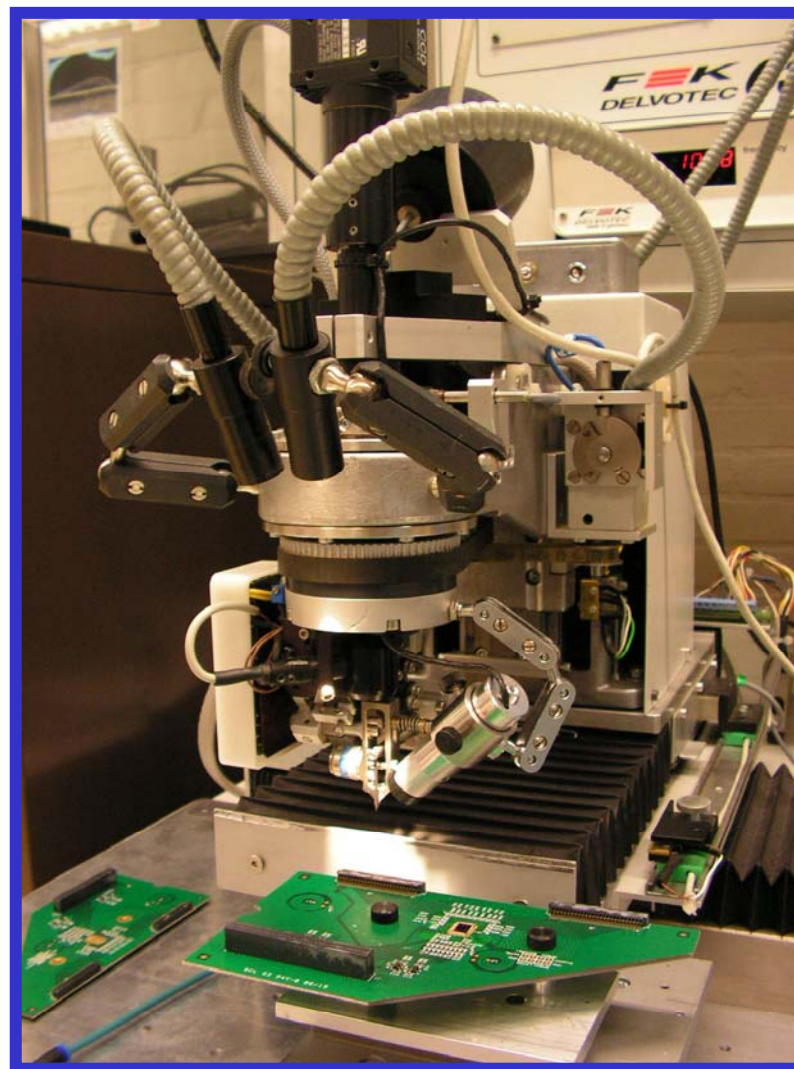
typical values: $0.5 \text{ bins} < \text{DNL} < 1.5 \text{ bins}$)

Buffer overflow recognized?

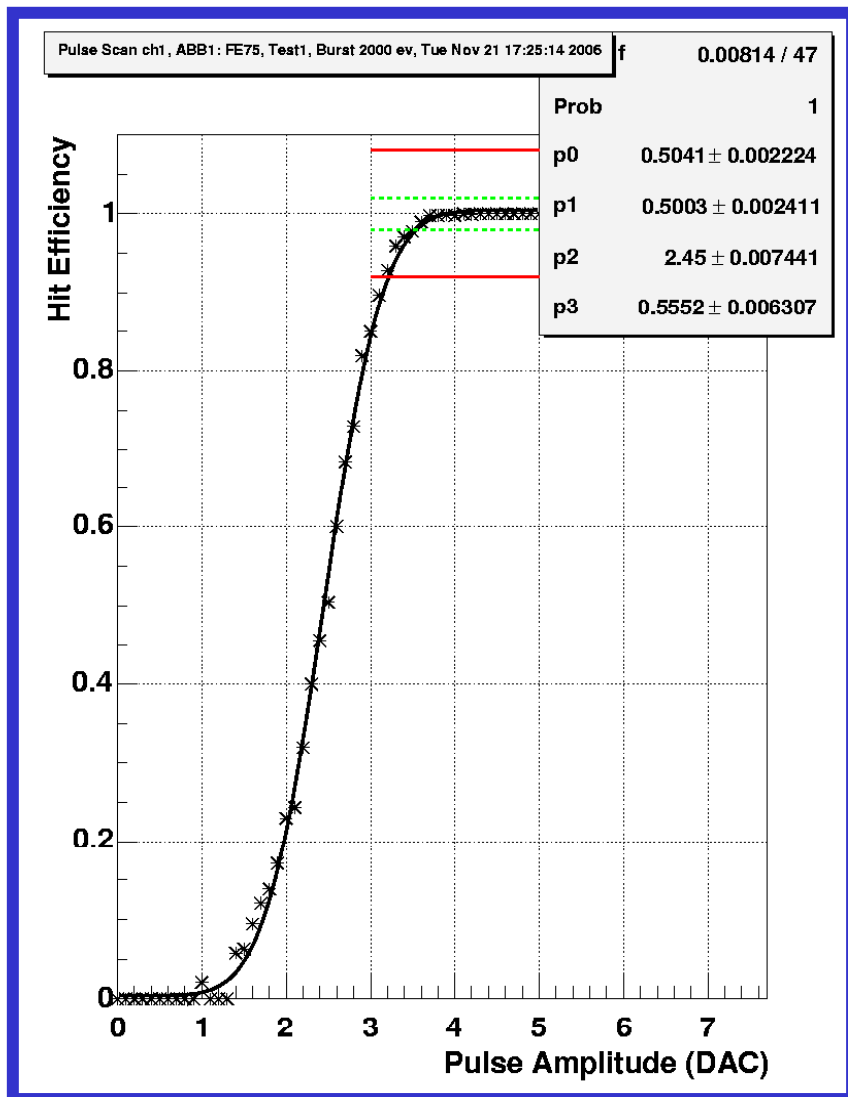
DAC's functional?



Solid silver-filled epoxy glue
Ultrasonic Soldering (~16 gr/wire)
Semi-Automatic procedure (~120 s)
Visual Inspection (1-2% repaired)



- **I2C test** (test of the OTIS register)
- **ADC Test** (Set the ASDDAC of the OTIS and measuring the output voltage)
- **ID Odd** (check if the data set is received correctly)
- **L0 Reset** (Check the data receiver)
- **Event ID distributions** (Flatness distribution with random trigger)
- **Header Bits** (Comparison with standard default header)
- **Event count Reset** (Check of the number of triggers received)
- **Power Up Reset** (Check the DAC register)
- **Id Even** (Check if the data set is received correctly)
- **Hit Map Odd/Even** (Check of the number of valid hits)



If,

$$g(Q_{in}) = V_{off} + G \cdot Q_{in}$$

Then,

$$Pr[V_{thr}, Q_i] = \frac{1}{2} + \frac{1}{2} Erf \left[\frac{Q_i - Q_{thr}}{\sqrt{2} ENC} \right]$$

Where,

$$Q_{thr} = \frac{V_{thr} - V_{off}}{G}$$

- Q_{thr} Global Uniformity
- **ENC** Direct measurement of Equivalent Noise Charge (fC)